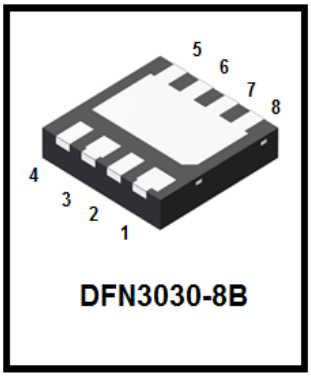
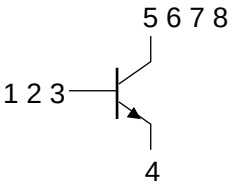
LBSS4350Q3T1G
S-LBSS4350Q3T1G

50V NPN Transistor



1. FEATURES

- We declare that the material of product are Halogen Free and compliance with RoHS requirements.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low collector-emitter saturation voltage.
- High collector current capability.
- High collector current gain.
- Higher efficiency leading to less heat generation.



2.APPLICATIONS

- Driver stages of audio and video amplifiers.

3. ORDERING INFORMATION

Device	Marking	Shipping
S-LBSS4350Q3T1G	S3	3000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25ºC unless otherwise stated)

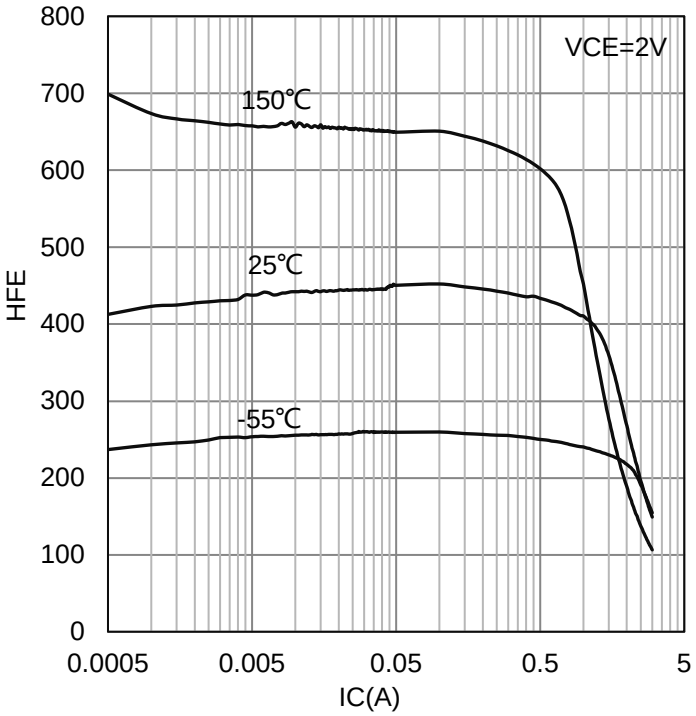
Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	50	V
Collector–Base Voltage	VCBO	60	V
Emitter–Base Voltage	VEBO	5	V
Collector Current	IC	3	A
Base Current	IB	0.5	A
Maximum Power Dissipation	PD	2	W
Thermal Resistance-Junction to Ambient	RθJA	65	℃/W
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-55~+150	℃

5. ELECTRICAL CHARACTERISTICS

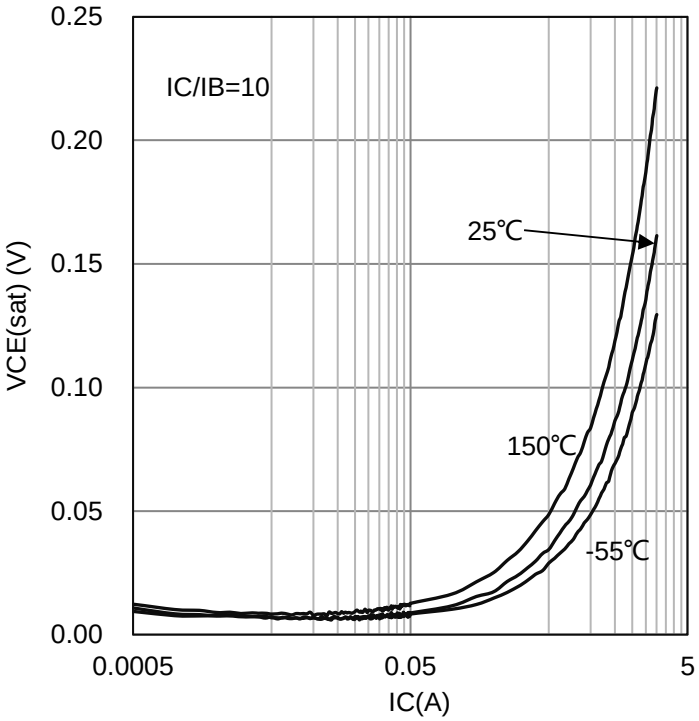
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 1 mA,IB = 0)	VBR(CEO)	50	-	-	V
Collector–Base Breakdown Voltage (IC = 100 μA,IE = 0)	VBR(CBO)	60	-	-	V
Emitter–Base Breakdown Voltage (IE = 100 μA,IC = 0)	VBR(EBO)	5	-	-	V
Collector-Base Cutoff Current (VCB =50 V,IE = 0)	ICBO	-	-	100	nA
Emitter-Base Cutoff Current (VEB=5V,IC=0)	IEBO	-	-	100	nA
Collector-Emitter cutoff Current (VCE= 50V,IB=0)	ICEO	-	-	10	μA
DC Current Gain (VCE=2V,IC=100mA) (VCE=2V,IC=500mA) (VCE=2V,IC=1A) (VCE=2V,IC=2A) (VCE=2V,IC=3A)	hFE	 300 300 300 200 100	 - - - - -	 - - - - -	
Collector–Emitter Saturation Voltage (IC=500mA,IB=50mA) (IC=1A,IB=50mA) (IC=2A,IB=100mA) (IC=2A,IB=200mA) (IC=3A,IB=300mA)	VCE(sat)	 - - - - -	 - - - - -	 80 160 280 260 370	mV
Base-emitter saturation voltage (IC=2A,IB=100mA) (IC=3A,IB=300mA)	VBE(sat)	 - -	 - -	 1.1 1.2	V
Transition frequency (IC=100mA,VCE=5V,f=100MHZ)	fT	100	-	-	MHz
Collector capacitance (IB=IE=0,VCB=10V,f=1MHZ)	Cc	-	25	-	pF

1. Pulse test: tp ⩽ 300 μs,δ ⩽ 0.02;

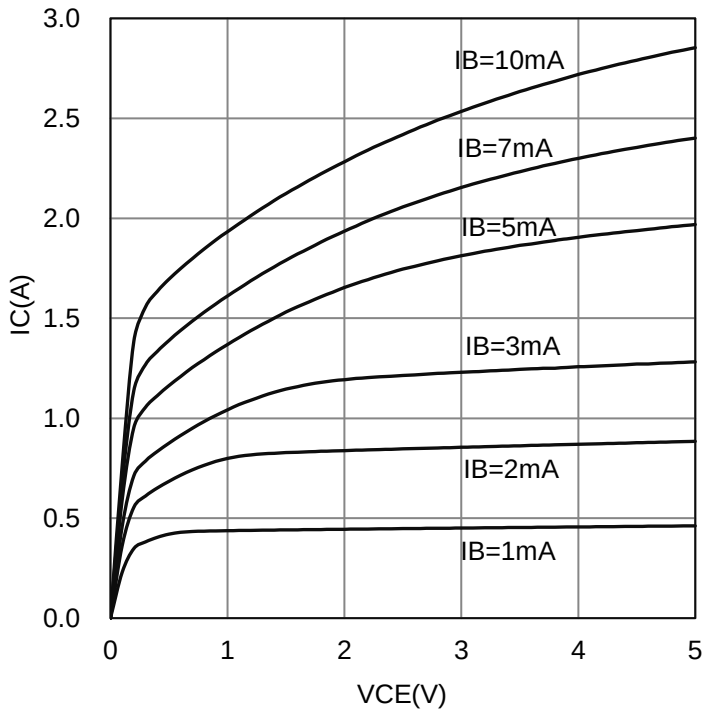
6.ELECTRICAL CHARACTERISTICS CURVES



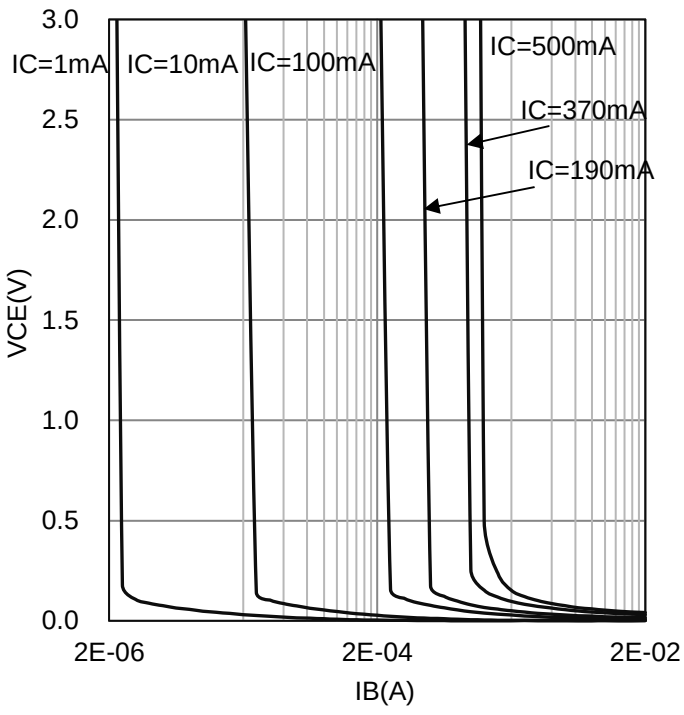
HFE vs. IC



VCE(sat) vs. IC

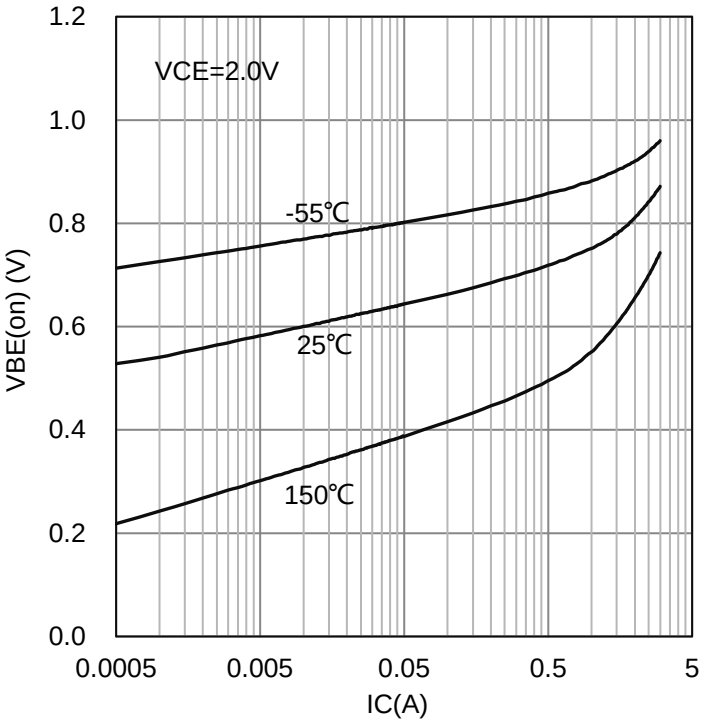


IC vs. VCE

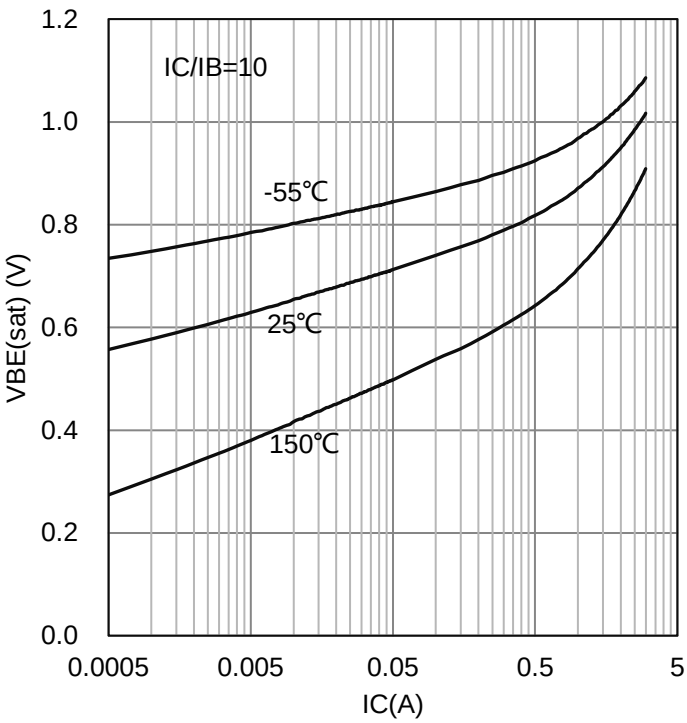


VCE vs. IB

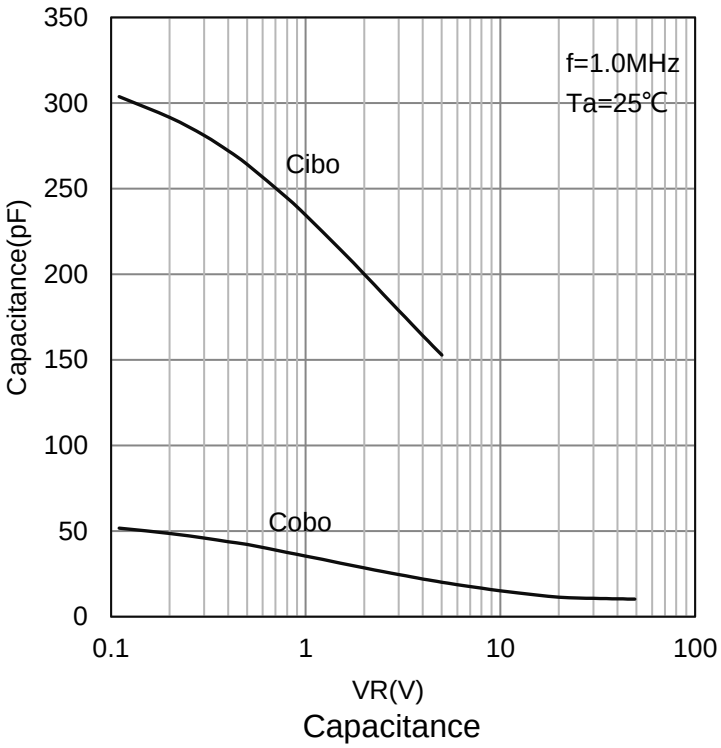
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



VBE(on) vs. IC

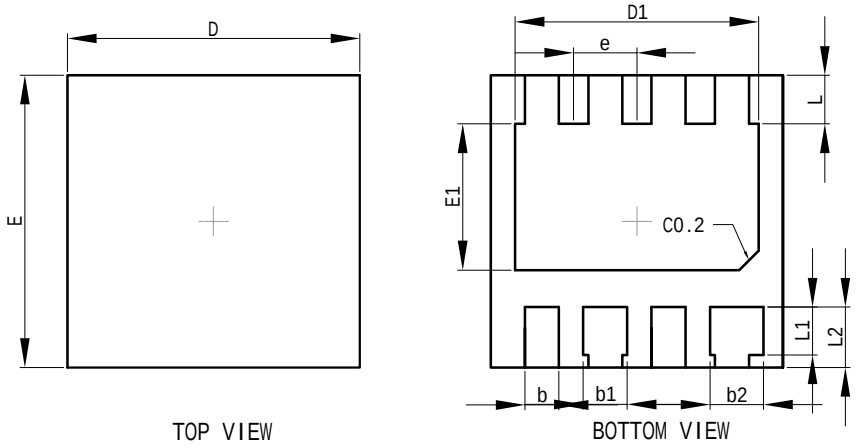


VBE(sat) vs. IC



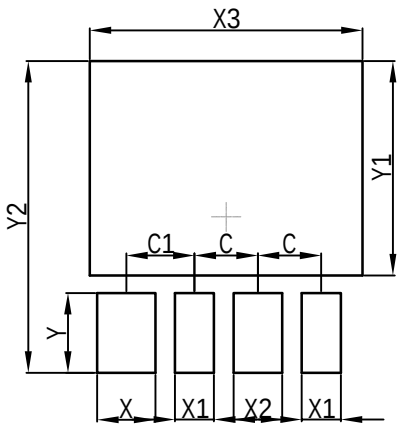
Capacitance

7.OUTLINE AND DIMENSIONS



DFN3030-8B			
Dim	Min	Nor	Max
A	0.60	0.65	0.70
A1	0.00	0.03	0.05
b	0.30	0.35	0.40
b1	0.40	0.45	0.50
b2	0.50	0.55	0.60
D	2.95	3.00	3.05
E	2.95	3.00	3.05
D1	2.45	2.50	2.55
E1	1.45	1.50	1.55
e	0.65BSC		
L	0.45	0.50	0.55
L1	0.44	0.49	0.54
L2	0.57	0.62	0.67
A3	0.152REF.		
All Dimensions in mm			

8.SOLDERING FOOTPRINT



DFN3030-8B	
Dim	(mm)
C	0.65
C1	0.70
X	0.60
X1	0.40
X2	0.50
X3	2.80
Y1	2.20
Y2	3.20
Y	0.82

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